

Abstracts

High performance 60-GHz coplanar MMIC LNA using InP heterojunction FETs with AlAs/InAs superlattice layer

A. Fujihara, E. Mizuki, H. Miyamoto, Y. Makino, K. Yamanoguchi and N. Samoto. "High performance 60-GHz coplanar MMIC LNA using InP heterojunction FETs with AlAs/InAs superlattice layer." 2000 Radio Frequency Integrated Circuits (RFIC) Symposium 00. (2000 [RFIC]): 213-216.

We describe a 60-GHz coplanar MMIC low-noise amplifier (LNA) using 0.1 μm -gate-length InP heterojunction FETs (HJFETs). An optimum gate width of 80 μm was determined for the first stage FET by using a small signal model including accurate scaling of the gate resistance. On-wafer noise measurements demonstrated a noise figure of 2.2 dB and a gain of 22.8 dB at 60 GHz.

 [Return to main document.](#)